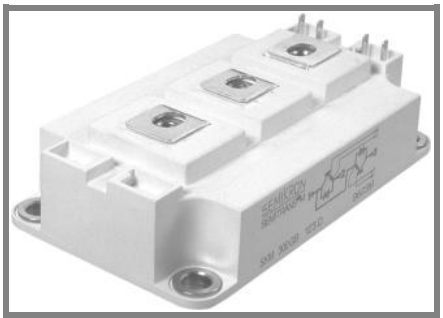
SKM 200GB063D



SEMITRANS® 3

Superfast NPT-IGBT Modules

SKM 200GB063D

Features

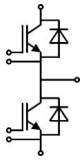
- N channel, homogeneous Silicon structure (NPT - Non punch-through IGBT)
- Low tail current with low temperature dependence
- High short circuit capability, self limiting if term. G is clamped to E
- Pos. temp.-coeff. of V_{CEsat}
- 50 % less turn off losses
- 30 % less short circuit current
- Very low C_{ies}, C_{oes}, C_{res}
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications

- Switched mode power supplies
- AC inverter servo drives
- UPS uninterruptable power supplies
- Welding inverters

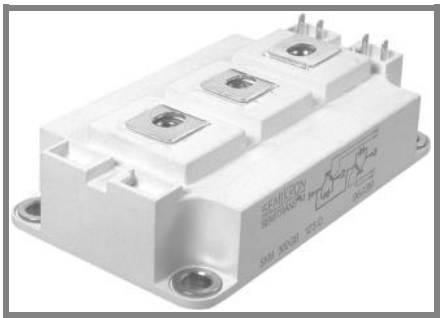
Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		600	V
I_C	T_j = 150 °C	T_{case} = 25 °C	260	A
		T_{case} = 70 °C	200	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		400	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 300 V; $V_{GE} \leq$ 20 V; V_{CES} < 600 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	200	A
		T_{case} = 80 °C	135	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		400	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	1400	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40 ... + 150	°C
T_{stg}			- 40 ... + 125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 4 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,1	0,3	mA
V_{CE0}		T_j = 25 °C		1,05		V
		T_j = 125 °C		1		V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		5,3		mΩ
		T_j = 125°C		7		mΩ
$V_{CE(sat)}$	I_{Cnom} = 200 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		2,1	2,5	V
		T_j = 125°C$_{chiplev.}$		2,4	2,8	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		11,2		nF
C_{oes}				1,25		nF
C_{res}				0,75		nF
Q_G	V_{GE} = 0V - +15V			480		nC
R_{Gint}	T_j = °C			0		Ω
$t_{d(on)}$	R_{Gon} = 8 Ω	V_{CC} = 300V		140		ns
t_r		I_{Cnom}= 200A		70		ns
E_{on}		T_j = 125 °C		11		mJ
$t_{d(off)}$	R_{Goff} = 8 Ω	V_{GE} = ±15V		442		ns
t_f				45		ns
E_{off}				7,5		mJ
$R_{th(j-c)}$	per IGBT				0,14	K/W



GB

SKM 200GB063D



SEMITRANS® 3

Superfast NPT-IGBT Modules

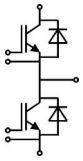
SKM 200GB063D

Features

- N channel, homogeneous Silicon structure (NPT - Non punch-through IGBT)
- Low tail current with low temperature dependence
- High short circuit capability, self limiting if term. G is clamped to E
- Pos. temp.-coeff. of V_{CEsat}
- 50 % less turn off losses
- 30 % less short circuit current
- Very low C_{ies}, C_{oes}, C_{res}
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications

- Switched mode power supplies
- AC inverter servo drives
- UPS uninterruptable power supplies
- Welding inverters

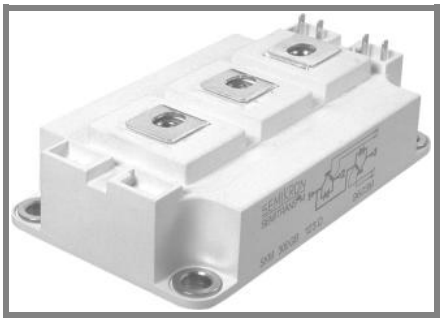


GB

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 200 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,55	1,9	V
		T_j = 125 °$C_{chiplev.}$		1,55		V
V_{F0}		T_j = 125 °C			0,9	V
r_F		T_j = 125 °C		4	5,5	mΩ
I_{RRM}	I_{Fnom} = 200 A	T_j = 125 °C		75		A
Q_{rr}				12,7		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,3	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M6		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



SEMITRANS® 3

Superfast NPT-IGBT Modules

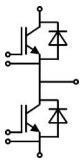
SKM 200GB063D

Features

- N channel, homogeneous Silicon structure (NPT - Non punch-through IGBT)
- Low tail current with low temperature dependence
- High short circuit capability, self limiting if term. G is clamped to E
- Pos. temp.-coeff. of V_{CEsat}
- 50 % less turn off losses
- 30 % less short circuit current
- Very low C_{ies}, C_{oes}, C_{res}
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications

- Switched mode power supplies
- AC inverter servo drives
- UPS uninterruptable power supplies
- Welding inverters



GB

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	90	mk/W
R_i	i = 2	39	mk/W
R_i	i = 3	9	mk/W
R_i	i = 4	2	mk/W
tau_i	i = 1	0,0416	s
tau_i	i = 2	0,0139	s
tau_i	i = 3	0,0021	s
tau_i	i = 4	0,0001	s
$Z_{th(j-c)D}$			
R_i	i = 1	200	mk/W
R_i	i = 2	84	mk/W
R_i	i = 3	14	mk/W
R_i	i = 4	2	mk/W
tau_i	i = 1	0,0275	s
tau_i	i = 2	0,0413	s
tau_i	i = 3	0,0019	s
tau_i	i = 4	0,004	s

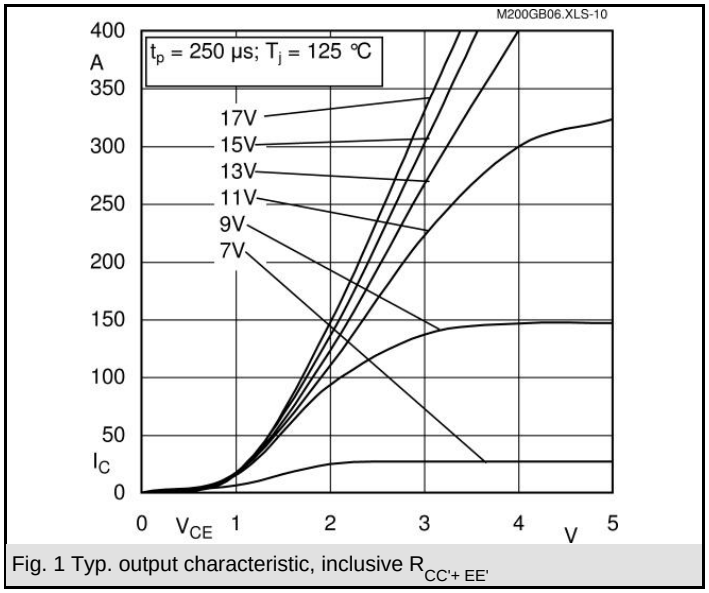


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

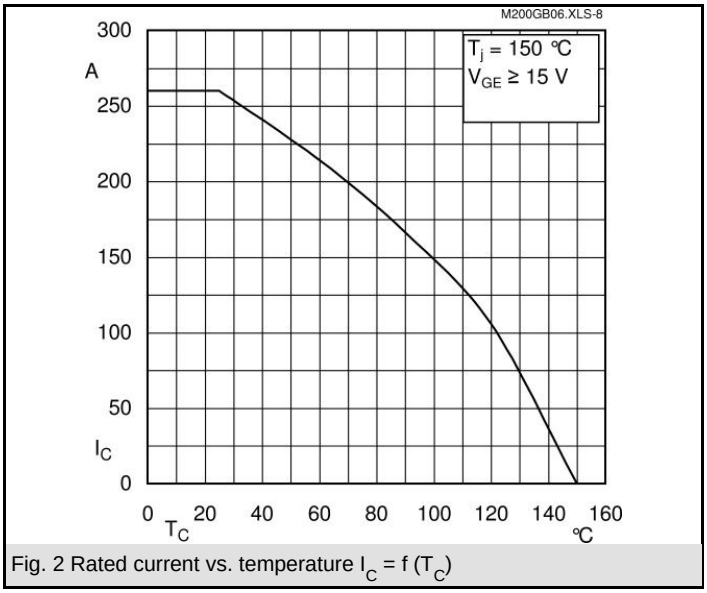


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

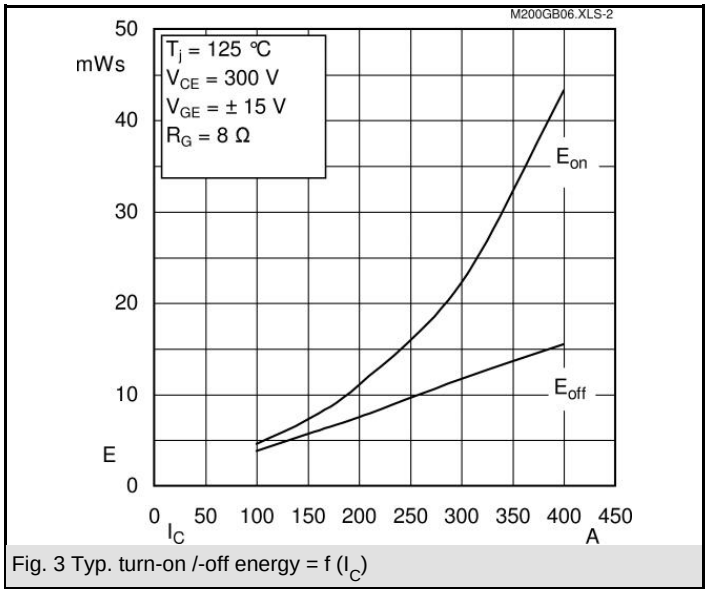


Fig. 3 Typ. turn-on /-off energy = f (I_C)

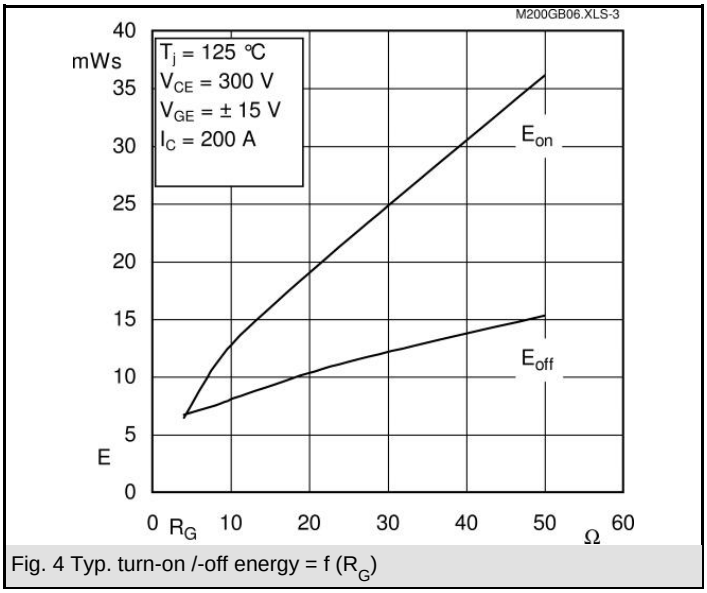


Fig. 4 Typ. turn-on /-off energy = f (R_G)

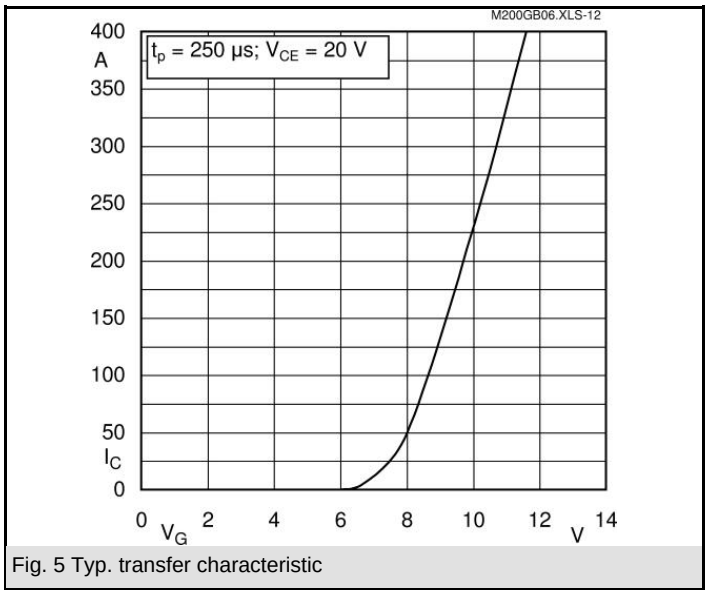


Fig. 5 Typ. transfer characteristic

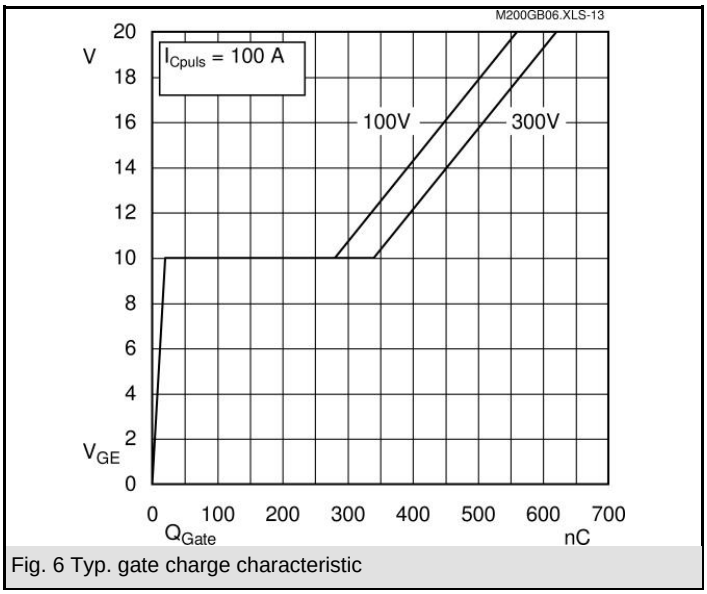


Fig. 6 Typ. gate charge characteristic

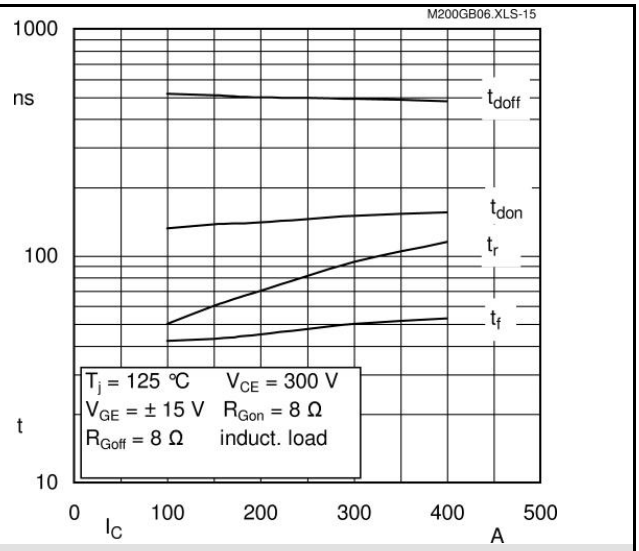


Fig. 7 Typ. switching times vs. I_C

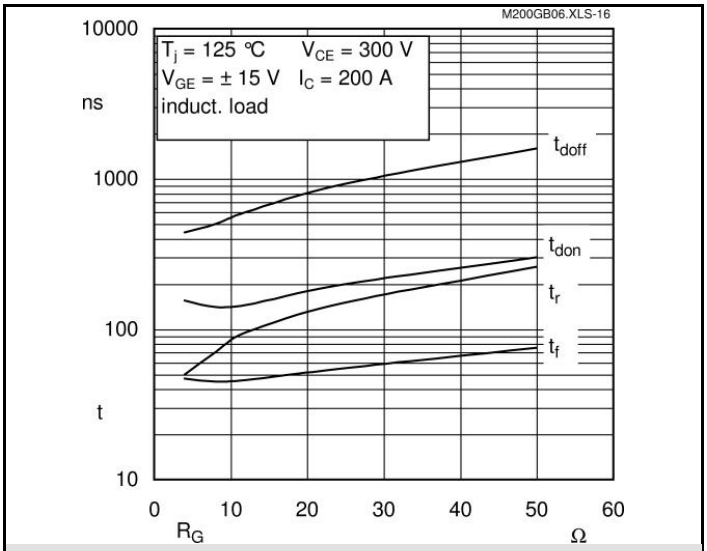


Fig. 8 Typ. switching times vs. gate resistor R_G

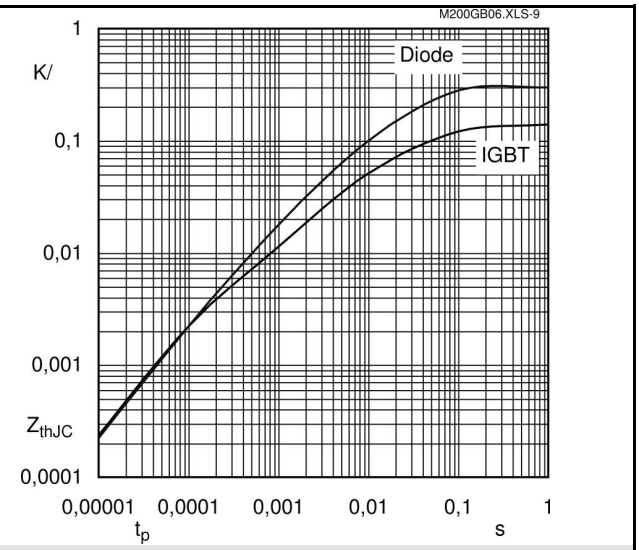


Fig. 9 Transient thermal impedance of IGBT and Diode

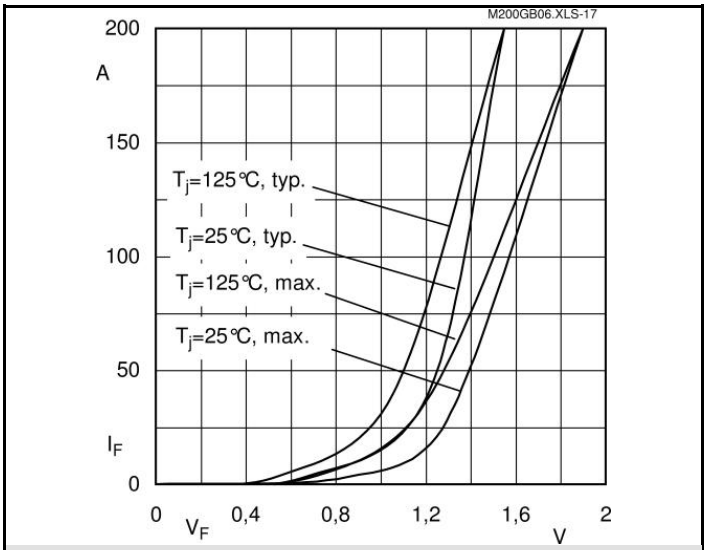


Fig. 10 CAL diode forward characteristic

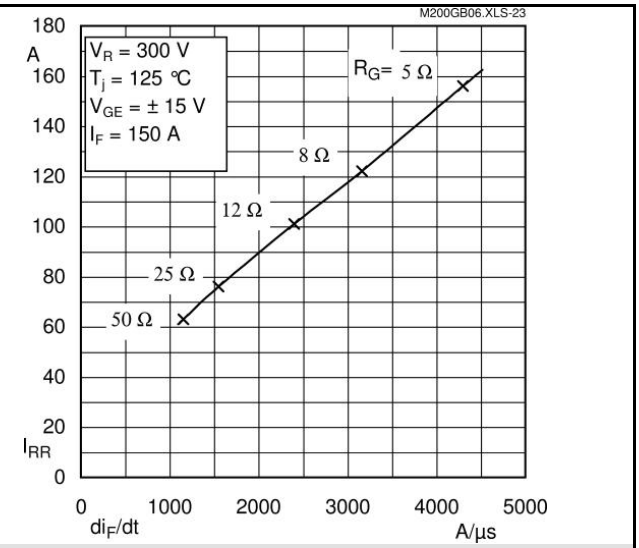


Fig. 11 Typ. CAL diode peak reverse recovery current

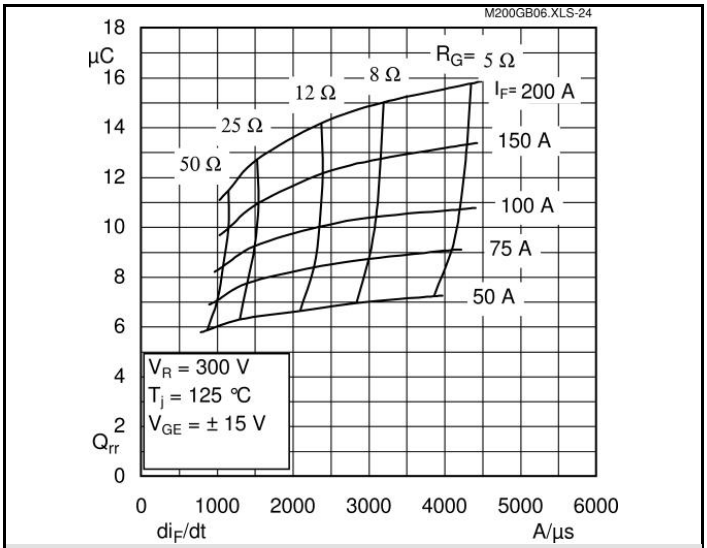
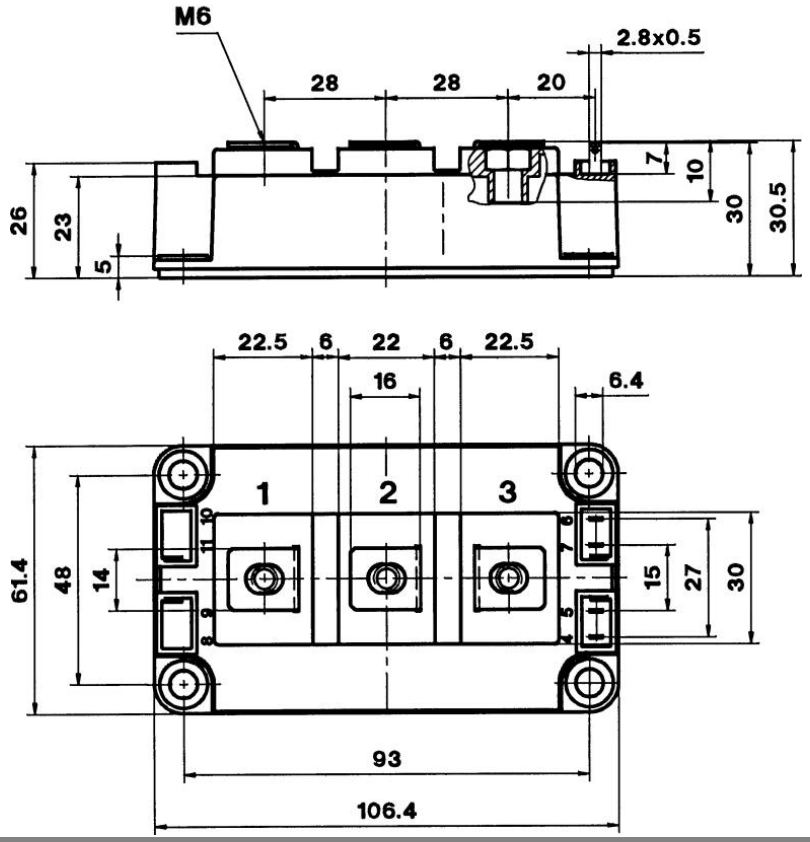


Fig. 12 Typ. CAL diode recovered charge

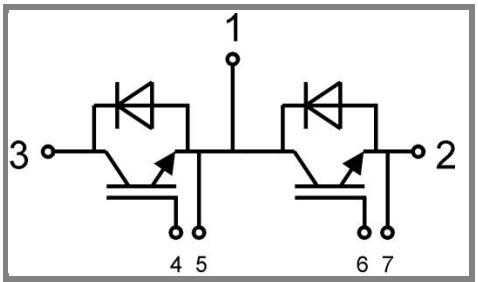
SKM 200GB063D

UL recognized File no. E 63 532

CASED56



Case D 56



GB Case D 56

